#### • Timers

- One 6-channel FlexTimer/PWM (FTM)
- Two 2-channel FlexTimer/PWM (FTM)
- One 2-channel periodic interrupt timer (PIT)
- One real-time clock (RTC)

#### • Communication interfaces

- Two SPI modules (SPI)
- Up to three UART modules (UART)
- One I2C module (I2C)

#### · Package options

- 64-pin QFP/LQFP
- 44-pin LQFP
- 32-pin LQFP
- 32-pin QFN

2 NXP Semiconductors

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# 1 Ordering parts

## 1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to **nxp.com** and perform a part number search for the following device numbers: KE02Z.

#### 2 Part identification

## 2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

#### 2.2 Format

Part numbers for this device have the following format:

Q KE## A FFF R T PP CC N

## 2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values				
Q	Qualification status	<ul> <li>M = Fully qualified, general market flow</li> <li>P = Prequalification</li> </ul>				
KE##	Kinetis family	• KE02				
А	Key attribute	• Z = M0+ core				
FFF	Program flash memory size	<ul> <li>16 = 16 KB</li> <li>32 = 32 KB</li> <li>64 = 64 KB</li> </ul>				
R	Silicon revision	<ul><li>(Blank) = Main</li><li>A = Revision after main</li></ul>				

Field	Description	Values
Т	Temperature range (°C)	• V = -40 to 105
PP	Package identifier	<ul> <li>LC = 32 LQFP (7 mm x 7 mm)</li> <li>FM = 32 QFN (5 mm x 5 mm)</li> <li>LD = 44 LQFP (10 mm x 10 mm)</li> <li>QH = 64 QFP (14 mm x 14 mm)</li> <li>LH = 64 LQFP (10 mm x 10 mm)</li> </ul>
CC	Maximum CPU frequency (MHz)	• 4 = 40 MHz
N	Packaging type	<ul><li>R = Tape and reel</li><li>(Blank) = Trays</li></ul>

## 2.4 Example

This is an example part number:

MKE02Z64VQH4

#### 3 Parameter classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 1. Parameter classifications

Р	Those parameters are guaranteed during production testing on each individual device.
С	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
Т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

#### **NOTE**

The classification is shown in the column labeled "C" in the parameter tables where appropriate.

# 4 Ratings

## 4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T <sub>STG</sub>	Storage temperature	<b>-</b> 55	150	°C	1
T <sub>SDR</sub>	Solder temperature, lead-free	_	260	°C	2

- 1. Determined according to JEDEC Standard JESD22-A103, High Temperature Storage Life.
- Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

## 4.2 Moisture handling ratings

Symbol	pol Description		Max.	Unit	Notes
MSL	Moisture sensitivity level	1	3		1

 Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

## 4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
$V_{HBM}$	Electrostatic discharge voltage, human body model	-6000	+6000	V	1
V <sub>CDM</sub>	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I <sub>LAT</sub>	Latch-up current at ambient temperature of 125°C	-100	+100	mA	3

- Determined according to JEDEC Standard JESD22-A114, Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM).
- 2. Determined according to JEDEC Standard JESD22-C101, Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components.
- 3. Determined according to JEDEC Standard JESD78D, IC Latch-up Test.
  - Test was performed at 125 °C case temperature (Class II).
  - I/O pins pass ±100 mA I-test with I<sub>DD</sub> current limit at 800 mA.
  - $\bullet~$  I/O pins pass +60/-100 mA I-test with  $I_{DD}$  current limit at 1000 mA.
  - Supply groups pass 1.5 V<sub>ccmax</sub>.
  - RESET pin was only tested with negative I-test due to product conditioning requirement.

## 4.4 Voltage and current operating ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in the following table may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this document.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either  $V_{SS}$  or  $V_{DD}$ ) or the programmable pullup resistor associated with the pin is enabled.

**Symbol Description** Min. Max. Unit ٧ 6.0  $V_{DD}$ Digital supply voltage -0.3120  $I_{DD}$ Maximum current into V<sub>DD</sub> mΑ  $V_{DD} + 0.3^{1}$ ٧  $V_{IN}$ Input voltage except true open drain pins -0.3-0.3Input voltage of true open drain pins -25  $I_D$ Instantaneous maximum current single pin limit (applies to all 25 mΑ port pins)  $V_{DDA}$ Analog supply voltage  $V_{DD} - 0.3$  $V_{DD} + 0.3$ V

Table 2. Voltage and current operating ratings

#### 5 General

## 5.1 Nonswitching electrical specifications

#### 5.1.1 DC characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 3. DC characteristics

Symbol	С	Descriptions	Descriptions		Typical <sup>1</sup>	Max	Unit
_	_	Operating voltage <sup>2</sup>	_	2.7	_	5.5	V

<sup>1.</sup> Maximum rating of V<sub>DD</sub> also applies to V<sub>IN</sub>.

#### Nonswitching electrical specifications

Table 3. DC characteristics (continued)

Symbol	С		Descriptions		Min	Typical <sup>1</sup>	Max	Unit
V <sub>OH</sub>	Р	Output	All I/O pins, except PTA2	5 V, I <sub>load</sub> = -5 mA	V <sub>DD</sub> – 0.8	_	_	V
	С	high voltage	and PTA3, standard- drive strength	3 V, $I_{load} = -2.5 \text{ mA}$	V <sub>DD</sub> – 0.8	_	_	V
	Р		High current drive pins,	5 V, $I_{load} = -20 \text{ mA}$	$V_{DD} - 0.8$	_	_	V
	С		high-drive strength <sup>3</sup>	$3 \text{ V}, \text{ I}_{\text{load}} = -10 \text{ mA}$	$V_{DD} - 0.8$	_	_	V
I <sub>OHT</sub>	D	Output	Max total I <sub>OH</sub> for all ports	5 V	_	_	-100	mA
		high current		3 V	_	_	-60	
V <sub>OL</sub>	Р	Output	All I/O pins, standard-	5 V, I <sub>load</sub> = 5 mA	_	_	8.0	V
	С	low voltage	drive strength	3 V, $I_{load} = 2.5 \text{ mA}$	_	_	8.0	V
	Р		High current drive pins,	5 V, I <sub>load</sub> =20 mA	<u> </u>	_	8.0	V
	С		high-drive strength <sup>3</sup>	$3 \text{ V}, I_{load} = 10 \text{ mA}$	_	_	8.0	V
I <sub>OLT</sub>	D	Output	Max total I <sub>OL</sub> for all ports	5 V	<u> </u>	_	100	mA
		low current		3 V	_	_	60	
V <sub>IH</sub>	Р	Input	All digital inputs	4.5≤V <sub>DD</sub> <5.5 V	$0.65 \times V_{DD}$	_	_	٧
		high voltage		2.7≤V <sub>DD</sub> <4.5 V	$0.70 \times V_{DD}$	_	_	
V <sub>IL</sub>	V <sub>IL</sub> P Input low voltage		All digital inputs	4.5≤V <sub>DD</sub> <5.5 V	_	_	0.35 × V <sub>DD</sub>	V
				2.7≤V <sub>DD</sub> <4.5 V	_	_	0.30 × V <sub>DD</sub>	
V <sub>hys</sub>	С	Input hysteresi s	All digital inputs	_	0.06 × V <sub>DD</sub>	_	_	mV
II <sub>In</sub> I	Р	Input leakage current	Per pin (pins in high impedance input mode)	$V_{IN} = V_{DD}$ or $V_{SS}$	_	0.1	1	μΑ
II <sub>INTOT</sub> I	С	Total leakage combine d for all port pins	Pins in high impedance input mode	$V_{IN} = V_{DD}$ or $V_{SS}$	_	_	2	μА
R <sub>PU</sub>	Р	Pullup resistors	All digital inputs, when enabled (all I/O pins other than PTA2 and PTA3)	_	30.0	_	50.0	kΩ
R <sub>PU</sub> <sup>4</sup>	Р	Pullup resistors	PTA2 and PTA3 pins	_	30.0	_	60.0	kΩ
I <sub>IC</sub>	D	DC	Single pin limit	$V_{IN} < V_{SS}, V_{IN} >$	-2	_	2	mA
		injection current <sup>5,</sup> 6, 7	Total MCU limit, includes sum of all stressed pins	V <sub>DD</sub>	-5	_	25	
C <sub>In</sub>	С	Input	capacitance, all pins	_	_	_	7	pF
V <sub>RAM</sub>	С	· -	M retention voltage	_	2.0	_	_	V
	1							

<sup>1.</sup> Typical values are measured at 25 °C. Characterized, not tested.

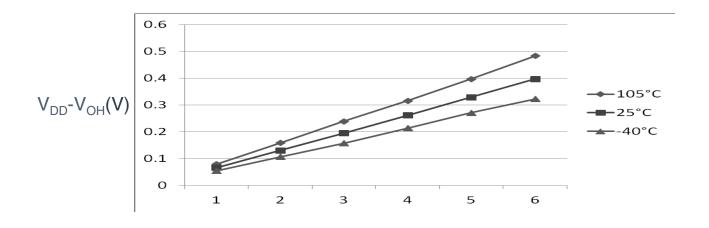
<sup>2.</sup> Maximum power supply VDD ramp-up rate is 70V/ms, characterized on samples of different lots.

- 3. Only PTB4, PTB5, PTD0, PTD1, PTE0, PTE1, PTH0, and PTH1 support high current output.
- 4. The specified resistor value is the actual value internal to the device. The pullup value may appear higher when measured externally on the pin.
- All functional non-supply pins, except for PTA2 and PTA3, are internally clamped to V<sub>SS</sub> and V<sub>DD</sub>. PTA2 and PTA3 are true
  open drain I/O pins that are internally clamped to V<sub>SS</sub>.
- 6. Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger value.
- 7. Power supply must maintain regulation within operating V<sub>DD</sub> range during instantaneous and operating maximum current conditions. If the positive injection current (V<sub>In</sub> > V<sub>DD</sub>) is higher than I<sub>DD</sub>, the injection current may flow out of V<sub>DD</sub> and could result in external power supply going out of regulation. Ensure that external V<sub>DD</sub> load will shunt current higher than maximum injection current when the MCU is not consuming power, such as when no system clock is present, or clock rate is very low (which would reduce overall power consumption).

Table 4. LVD and POR specification

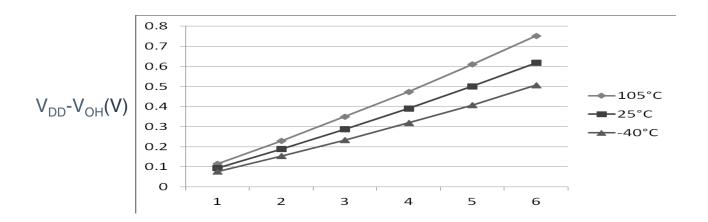
Symbol	С	Desc	ription	Min	Тур	Max	Unit
V <sub>POR</sub>	D	POR re-ai	m voltage <sup>1</sup>	1.5	1.75	2.0	V
V <sub>LVDH</sub>	С	threshold—hig	Falling low-voltage detect threshold—high range (LVDV = 1) <sup>2</sup>		4.3	4.4	V
V <sub>LVW1H</sub>	С	Falling low- voltage	Level 1 falling (LVWV = 00)	4.3	4.4	4.5	V
V <sub>LVW2H</sub>	С	warning threshold— high range	Level 2 falling (LVWV = 01)	4.5	4.5	4.6	V
V <sub>LVW3H</sub>	С	riigii rarige	Level 3 falling (LVWV = 10)	4.6	4.6	4.7	V
V <sub>LVW4H</sub>	С		Level 4 falling (LVWV = 11)	4.7	4.7	4.8	V
V <sub>HYSH</sub>	С		High range low-voltage detect/warning hysteresis		100	_	mV
V <sub>LVDL</sub>	С	threshold—lov	Falling low-voltage detect threshold—low range (LVDV = 0)		2.61	2.66	V
V <sub>LVW1L</sub>	С	Falling low- voltage	Level 1 falling (LVWV = 00)	2.62	2.7	2.78	V
V <sub>LVW2L</sub>	С	warning threshold— low range	Level 2 falling (LVWV = 01)	2.72	2.8	2.88	V
V <sub>LVW3L</sub>	С	— low range	Level 3 falling (LVWV = 10)	2.82	2.9	2.98	V
V <sub>LVW4L</sub>	С		Level 4 falling (LVWV = 11)	2.92	3.0	3.08	V
V <sub>HYSDL</sub>	С		Low range low-voltage detect hysteresis		40	_	mV
V <sub>HYSWL</sub>	С		Low range low-voltage warning hysteresis		80	_	mV
V <sub>BG</sub>	Р	Buffered ban	dgap output 3	1.14	1.16	1.18	V

- 1. Maximum is highest voltage that POR is guaranteed.
- 2. Rising thresholds are falling threshold + hysteresis.
- 3. voltage Factory trimmed at  $V_{DD} = 5.0 \text{ V}$ , Temp = 25 °C



I<sub>OH</sub>(mA)

Figure 1. Typical  $V_{DD}$ - $V_{OH}$  Vs.  $I_{OH}$  (standard drive strength) ( $V_{DD}$  = 5 V)



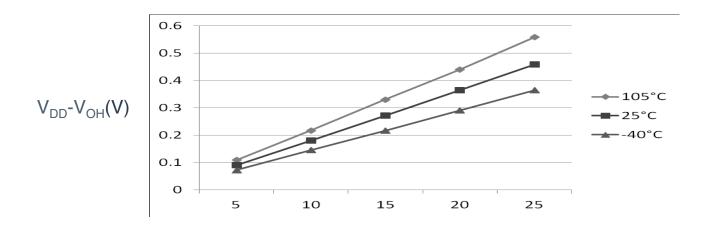
 $I_{OH}(mA)$ 

Figure 2. Typical  $V_{DD}$ - $V_{OH}$  Vs.  $I_{OH}$  (standard drive strength) ( $V_{DD}$  = 3 V)

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 $I_{OH}(mA)$  Figure 3. Typical  $V_{DD}$ - $V_{OH}$  Vs.  $I_{OH}$  (high drive strength) ( $V_{DD}$  = 5 V)

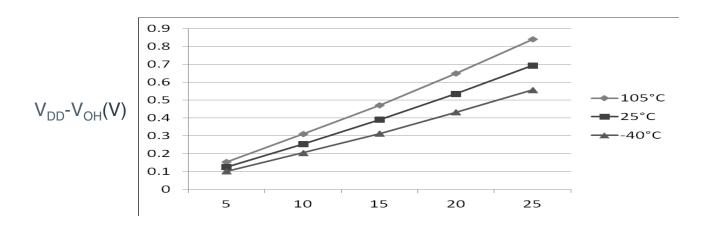
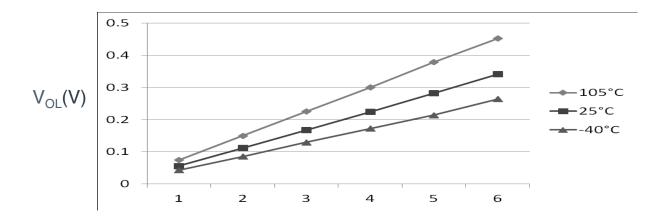


Figure 4. Typical  $V_{DD}$ - $V_{OH}$  Vs.  $I_{OH}$  (high drive strength) ( $V_{DD}$  = 3 V)

 $I_{OH}(mA)$ 

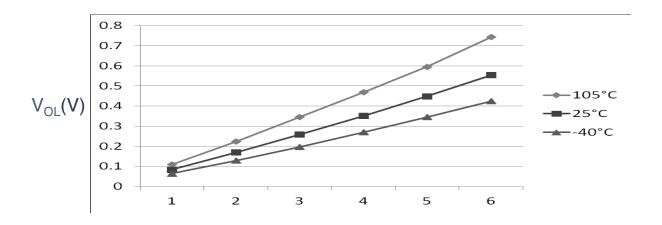
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 $I_{OL}(mA)$ 

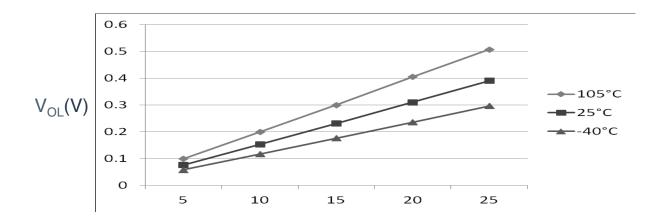
Figure 5. Typical  $V_{OL}$  Vs.  $I_{OL}$  (standard drive strength) ( $V_{DD} = 5 \text{ V}$ )



 $I_{OL}(mA)$ 

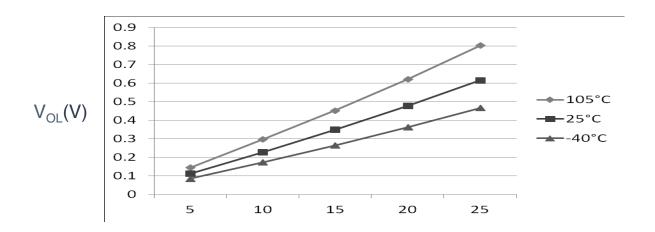
Figure 6. Typical  $V_{OL}$  Vs.  $I_{OL}$  (standard drive strength) ( $V_{DD}$  = 3 V)

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 $I_{OL}(mA)$ 

Figure 7. Typical  $V_{OL}$  Vs.  $I_{OL}$  (high drive strength) ( $V_{DD} = 5 \text{ V}$ )



 $I_{OL}(mA)$ 

Figure 8. Typical  $V_{OL}$  Vs.  $I_{OL}$  (high drive strength) ( $V_{DD} = 3 \text{ V}$ )

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## 5.1.2 Supply current characteristics

This section includes information about power supply current in various operating modes.

Table 5. Supply current characteristics

С	Parameter	Symbol	Core/Bus Freq	V <sub>DD</sub> (V)	Typical <sup>1</sup>	Max <sup>2</sup>	Unit	Temp
С	Run supply current FEI	RI <sub>DD</sub>	40/20 MHz	5	7.8	_	mA	–40 to 105 °C
С	mode, all modules clocks enabled; run from flash		20/20 MHz		6.7	_		
С	chabled, full from hash		10/10 MHz		4.5	_		
			1/1 MHz		1.5	_		
С			40/20 MHz	3	7.7	_		
С			20/20 MHz		6.6	_		
С			10/10 MHz		4.4	_		
			1/1 MHz		1.45	_		
С	Run supply current FEI	RI <sub>DD</sub>	40/20 MHz	5	6.3	_	mA	–40 to 105 °C
С	mode, all modules clocks disabled; run from flash		20/20 MHz		5.3	_		
С	albabioa, rair iroin naoir		10/10 MHz		3.7	_		
			1/1 MHz		1.5	_		
С			40/20 MHz	3	6.2	_		
С			20/20 MHz		5.3	_		
С			10/10 MHz		3.7	_		
			1/1 MHz		1.4	_		
С	Run supply current FBE	$RI_{DD}$	40/20 MHz	5	10.3	_	mA	–40 to 105 °C
Р	mode, all modules clocks enabled; run from RAM		20/20 MHz		9	14.8		
С			10/10 MHz		5.2	_		
			1/1 MHz		1.45	_		
С			40/20 MHz	3	10.2	_		
Р			20/20 MHz		8.8	11.8		
С			10/10 MHz		5.1	_		
			1/1 MHz		1.4	_		
С	Run supply current FBE	$RI_DD$	40/20 MHz	5	8.9	_	mA	–40 to 105 °C
Р	mode, all modules clocks disabled; run from RAM		20/20 MHz		8	12.3		
С	aisabieu, full llolli HAW		10/10 MHz		4.4	_		
			1/1 MHz		1.35	_		
С			40/20 MHz	3	8.8	_		
Р			20/20 MHz		7.8	9.2		
С			10/10 MHz		4.2	_		
			1/1 MHz		1.3			

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Table 5. Supply current characteristics (continued)

С	Parameter	Symbol	Core/Bus Freq	V <sub>DD</sub> (V)	Typical <sup>1</sup>	Max <sup>2</sup>	Unit	Temp
С	Wait mode current FEI	WI <sub>DD</sub>	40/20 MHz	5	6.4	_	mA	–40 to 105 °C
Р	mode, all modules clocks enabled		20/20 MHz		5.5	_		
С	Chabled		20/10 MHz		3.5	_		
			1/1 MHz		1.4	_		
С			40/20 MHz	3	6.3	_		
С			20/20 MHz		5.4	_		
			10/10 MHz		3.4	_		
			1/1 MHz		1.4	_		
Р	Stop mode supply current	SI <sub>DD</sub>	_	5	2	85	μΑ	–40 to 105 °C
Р	no clocks active (except 1 kHz LPO clock) <sup>3</sup>		_	3	1.9	80		–40 to 105 °C
С	ADC adder to Stop	_	_	5	86 (64-, 44-	_	μA	–40 to 105 °C
	ADLPC = 1				pin packages)			
	ADLSMP = 1				42 (32-pin			
	ADCO = 1				package)			
С	MODE = 10B			3	82 (64-, 44-	_		
	ADICLK = 11B				pin packages)			
					41 (32-pin package)			
С	ACMP adder to Stop	_	_	5	12	_	μA	–40 to 105 °C
С			_	3	12	_		
С	LVD adder to stop <sup>4</sup>	_	_	5	128	_	μΑ	–40 to 105 °C
С				3	124	_		

- 1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
- 2. The Max current is observed at high temperature of 105 °C.
- 3. RTC adder causes I<sub>DD</sub> to increase typically by less than 1 μA; RTC clock source is 1 kHz LPO clock.
- 4. LVD is periodically woken up from Stop by 5% duty cycle. The period is equal to or less than 2 ms.

#### 5.1.3 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependent on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation play a significant role in EMC performance. The system designer must consult the following applications notes, available on **nxp.com** for advice and guidance specifically targeted at optimizing EMC performance.

- AN2321: Designing for Board Level Electromagnetic Compatibility
- AN1050: Designing for Electromagnetic Compatibility (EMC) with HCMOS Microcontrollers

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#### **Switching specifications**

- AN1263: Designing for Electromagnetic Compatibility with Single-Chip Microcontrollers
- AN2764: Improving the Transient Immunity Performance of Microcontroller-Based Applications
- AN1259: System Design and Layout Techniques for Noise Reduction in MCU-Based Systems

# 5.1.3.1 EMC radiated emissions operating behaviors Table 6. EMC radiated emissions operating behaviors for 64-pin QFP package

Symbol	Description	Frequency band (MHz)	Тур.	Unit	Notes
V <sub>RE1</sub>	Radiated emissions voltage, band 1	0.15–50	14	dΒμV	1, 2
V <sub>RE2</sub>	Radiated emissions voltage, band 2	50–150	15	dΒμV	
V <sub>RE3</sub>	Radiated emissions voltage, band 3	150–500	3	dΒμV	
V <sub>RE4</sub>	Radiated emissions voltage, band 4	500-1000	4	dΒμV	
V <sub>RE_IEC</sub>	IEC level	0.15-1000	М	_	2, 3

- Determined according to IEC Standard 61967-1, Integrated Circuits Measurement of Electromagnetic Emissions, 150
  kHz to 1 GHz Part 1: General Conditions and Definitions and IEC Standard 61967-2, Integrated Circuits Measurement of
  Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband
  TEM Cell Method. Measurements were made while the microcontroller was running basic application code. The reported
  emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the
  measured orientations in each frequency range.
- 2.  $V_{DD} = 5.0 \text{ V}$ ,  $T_A = 25 \,^{\circ}\text{C}$ ,  $f_{OSC} = 10 \text{ MHz}$  (crystal),  $f_{BUS} = 20 \text{ MHz}$
- 3. Specified according to Annex D of IEC Standard 61967-2, Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method

# 5.2 Switching specifications

#### 5.2.1 Control timing

Table 7. Control timing

Num	С	Rating	)	Symbol	Min	Typical <sup>1</sup>	Max	Unit
1	D	System and core clock		f <sub>Sys</sub>	DC	_	40	MHz
2	Р	Bus frequency (t <sub>cyc</sub> = 1/f <sub>Bus</sub>	)	f <sub>Bus</sub>	DC	_	20	MHz
3	Р	Internal low power oscillato	r frequency	f <sub>LPO</sub>	0.67	1.0	1.25	KHz
4	D	External reset pulse width <sup>2</sup>	t <sub>extrst</sub>	1.5 ×	_	_	ns	
					t <sub>cyc</sub>			
5	D	Reset low drive		t <sub>rstdrv</sub>	$34 \times t_{cyc}$	_	_	ns
6	D	IRQ pulse width	Asynchronous path <sup>2</sup>	t <sub>ILIH</sub>	100	_	_	ns
	D		Synchronous path <sup>3</sup>	t <sub>IHIL</sub>	$1.5 \times t_{cyc}$	_	_	ns

Table 7.	Control	timing	(continued)
----------	---------	--------	-------------

Num	С	Rating	I	Symbol	Min	Typical <sup>1</sup>	Max	Unit
7	D	Keyboard interrupt pulse width Asynchronous path <sup>2</sup>		t <sub>ILIH</sub>	100	_	_	ns
	D		Synchronous path	t <sub>IHIL</sub>	$1.5 \times t_{cyc}$	_	_	ns
8	С	Port rise and fall time -	_	t <sub>Rise</sub>	_	10.2	_	ns
	С	Normal drive strength (load = 50 pF) <sup>4</sup>		t <sub>Fall</sub>	_	9.5	_	ns
	С	Port rise and fall time -	_	t <sub>Rise</sub>	_	5.4	_	ns
	high drive strength (load = 50 pF) <sup>4</sup>			t <sub>Fall</sub>	_	4.6	_	ns

- 1. Typical values are based on characterization data at  $V_{DD} = 5.0 \text{ V}$ , 25 °C unless otherwise stated.
- 2. This is the shortest pulse that is guaranteed to be recognized as a RESET pin request.
- 3. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized.
- 4. Timing is shown with respect to 20% V<sub>DD</sub> and 80% V<sub>DD</sub> levels. Temperature range -40 °C to 105 °C.

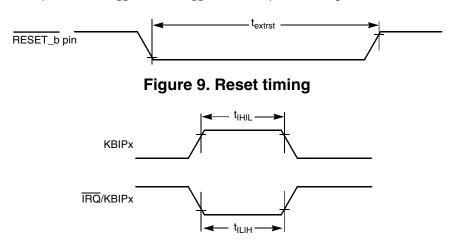


Figure 10. KBIPx timing

#### 5.2.2 FTM module timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 8. FTM input timing

С	Function	Symbol	Min	Max	Unit
D	External clock frequency	f <sub>TCLK</sub>	0	f <sub>Bus</sub> /4	Hz
D	External clock period	t <sub>TCLK</sub>	4	_	t <sub>cyc</sub>

Table 8. FTM input timing (continued)

С	Function	Symbol	Min	Max	Unit
D	External clock high time	t <sub>clkh</sub>	1.5	_	t <sub>cyc</sub>
D	External clock low time	t <sub>cikl</sub>	1.5	_	t <sub>cyc</sub>
D	Input capture pulse width	t <sub>ICPW</sub>	1.5	_	t <sub>cyc</sub>

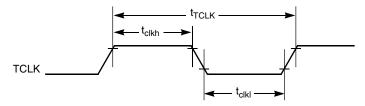


Figure 11. Timer external clock

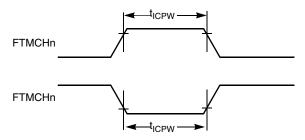


Figure 12. Timer input capture pulse

# 5.3 Thermal specifications

# 5.3.1 Thermal operating requirements

Table 9. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T <sub>J</sub>	Die junction temperature	-40	125	°C	
T <sub>A</sub>	Ambient temperature	-40	105	°C	1

1. Maximum  $T_A$  can be exceeded only if the user ensures that  $T_J$  does not exceed maximum  $T_J$ . The simplest method to determine  $T_J$  is:  $T_J = T_A + \theta_{JA} x$  chip power dissipation

#### 5.3.2 Thermal characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take  $P_{I/O}$  into account in power calculations, determine the difference between actual pin voltage and  $V_{SS}$  or  $V_{DD}$  and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and  $V_{SS}$  or  $V_{DD}$  will be very small.

Board type	Symbo I	Description	64 LQFP	64 QFP	44 LQFP	32 LQFP	32 QFN	Unit	Notes
Single-layer (1S)	$R_{ hetaJA}$	Thermal resistance, junction to ambient (natural convection)	71	61	75	86	97	°C/W	1, 2
Four-layer (2s2p)	$R_{ heta JA}$	Thermal resistance, junction to ambient (natural convection)	53	47	53	57	33	°C/W	1, 3
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	59	50	62	72	81	°C/W	1, 3
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	46	41	47	51	27	°C/W	1, 3
_	$R_{\theta JB}$	Thermal resistance, junction to board	35	32	34	33	12	°C/W	4
_	$R_{\theta JC}$	Thermal resistance, junction to case	20	23	20	24	1.3	°C/W	5
_	$\Psi_{ m JT}$	Thermal characterization parameter, junction to package top outside center (natural convection)	5	8	5	6	3	°C/W	6

Table 10. Thermal attributes

- Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
- 2. Per JEDEC JESD51-2 with the single layer board (JESD51-3) horizontal.
- 3. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
- 4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 5. Thermal resistance between the die and the solder pad on the bottom of the package. Interface resistance is ignored.
- 6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization.

The average chip-junction temperature (T<sub>J</sub>) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA})$$

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Where:

 $T_A = Ambient temperature, °C$ 

 $\theta_{JA}$  = Package thermal resistance, junction-to-ambient, °C/W

$$P_D = P_{int} + P_{I/O}$$

 $P_{int} = I_{DD} \times V_{DD}$ , Watts - chip internal power

 $P_{I/O}$  = Power dissipation on input and output pins - user determined

For most applications,  $P_{I/O} \ll P_{int}$  and can be neglected. An approximate relationship between  $P_D$  and  $T_I$  (if  $P_{I/O}$  is neglected) is:

$$P_D = K \div (T_I + 273 \, ^{\circ}C)$$

Solving the equations above for K gives:

$$K = P_D \times (T_A + 273 \text{ }^{\circ}C) + \theta_{JA} \times (P_D)^2$$

where K is a constant pertaining to the particular part. K can be determined by measuring  $P_D$  (at equilibrium) for an known  $T_A$ . Using this value of K, the values of  $P_D$  and  $P_D$  and  $P_D$  and  $P_D$  are obtained by solving the above equations iteratively for any value of  $P_D$ .

# 6 Peripheral operating requirements and behaviors

#### 6.1 Core modules

#### 6.1.1 SWD electricals

Table 11. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	5.5	V
J1	SWD_CLK frequency of operation			
	Serial wire debug	0	20	MHz
J2	SWD_CLK cycle period	1/J1	_	ns
J3	SWD_CLK clock pulse width			
	Serial wire debug	20	_	ns
J4	SWD_CLK rise and fall times	_	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	_	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	3	_	ns

Table 11. SWD full voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
J11	SWD_CLK high to SWD_DIO data valid	_	35	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	_	ns

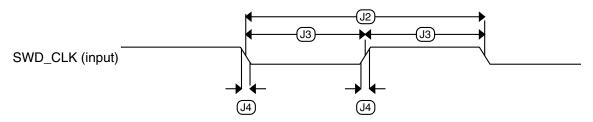


Figure 13. Serial wire clock input timing

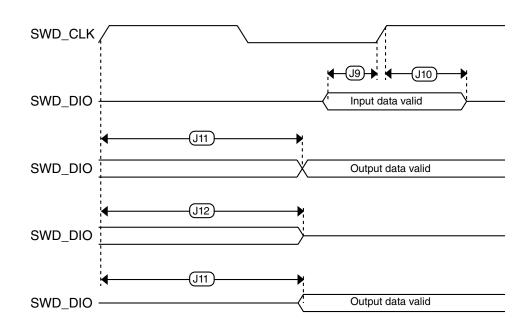


Figure 14. Serial wire data timing

# 6.2 External oscillator (OSC) and ICS characteristics

Table 12. OSC and ICS specifications (temperature range = -40 to 105 °C ambient)

Num	С	Characteristic		Symbol	Min	Typical <sup>1</sup>	Max	Unit
1	С	Crystal or	Low range (RANGE = 0)	f <sub>lo</sub>	31.25	32.768	39.0625	kHz
	С	resonator frequency	High range (RANGE = 1)	f <sub>hi</sub>	4	_	20	MHz

Peripheral operating requirements and behaviors

Table 12. OSC and ICS specifications (temperature range = -40 to 105  $^{\circ}$ C ambient) (continued)

Num	С	С	Characteristic	Symbol	Min	Typical <sup>1</sup>	Max	Unit
2	D	Lo	pad capacitors	C1, C2		See Note <sup>2</sup>		
3	D	Feedback resistor	Low Frequency, Low-Power Mode <sup>3</sup>	R <sub>F</sub>	_	_	_	ΜΩ
			Low Frequency, High-Gain Mode		_	10	_	ΜΩ
			High Frequency, Low- Power Mode		_	1	_	ΜΩ
			High Frequency, High-Gain Mode		_	1	_	ΜΩ
4	D	Series resistor -	Low-Power Mode <sup>3</sup>	R <sub>S</sub> <sup>2</sup>	_	0	_	kΩ
		Low Frequency	High-Gain Mode		_	200	_	kΩ
5	D	Series resistor - High Frequency	Low-Power Mode <sup>3</sup>	R <sub>S</sub> <sup>2</sup>	_	0	_	kΩ
	D	Series resistor -	4 MHz		_	0	_	kΩ
	D	High Frequency,	8 MHz		_	0	_	kΩ
	D	High-Gain Mode	16 MHz		_	0	_	kΩ
6	С	Crystal start-up	Low range, low power	t <sub>CSTL</sub>	_	1000	_	ms
	С	time low range	Low range, high gain		_	800	_	ms
	С	= 32.768 kHz crystal; High	High range, low power	t <sub>CSTH</sub>	_	3	_	ms
	c range = 20 MHz	High range, high gain		_	1.5	_	ms	
7	Т	Internal re	eference start-up time	t <sub>IRST</sub>	_	20	50	μs
8	Р	Internal reference	e clock (IRC) frequency trim range	f <sub>int_t</sub>	31.25	_	39.0625	kHz
9	Р	Internal reference clock frequency, factory trimmed	T = 25 °C, V <sub>DD</sub> = 5 V	f <sub>int_ft</sub>	_	31.25	_	kHz
10	Р	DCO output frequency range	FLL reference = fint_t, flo, or fhi/RDIV	f <sub>dco</sub>	32	_	40	MHz
11	Р	Factory trimmed internal oscillator accuracy <sup>6</sup>	T = 25 °C, V <sub>DD</sub> = 5 V	$\Delta f_{int\_ft}$	-0.5	_	0.5	%
12	С	Deviation of IRC over	Over temperature range from -40 °C to 105°C	$\Delta f_{int\_t}$	-1	_	0.5	%
		temperature when trimmed at T = 25 °C, $V_{DD}$ = 5 V	Over temperature range from 0 °C to 105°C	∆f <sub>int_t</sub>	-0.5	_	0.5	
13	С	Frequency accuracy of	Over temperature range from -40 °C to 105°C	$\Delta f_{dco_ft}$	-1.5	_	1	%
		DCO output using factory trim value	Over temperature range from 0 °C to 105°C	$\Delta f_{dco_ft}$	-1	_	1	

Table 12. OSC and ICS specifications (temperature range = -40 to 105 °C ambient) (continued)

Num	С	Characteristic	Symbol	Min	Typical <sup>1</sup>	Max	Unit
14	С	FLL acquisition time <sup>4,7</sup>	t <sub>Acquire</sub>	_	_	2	ms
15	С	Long term jitter of DCO output clock (averaged over 2 ms interval) <sup>8</sup>	C <sub>Jitter</sub>	_	0.02	0.2	%f <sub>dco</sub>

- 1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
- 2. See crystal or resonator manufacturer's recommendation.
- Load capacitors (C<sub>1</sub>,C<sub>2</sub>), feedback resistor (R<sub>F</sub>) and series resistor (R<sub>S</sub>) are incorporated internally when RANGE = HGO = 0
- 4. This parameter is characterized and not tested on each device.
- Proper PC board layout procedures must be followed to achieve specifications.
- 6. The accuracy is for factory trimmed deviation when performing trim process in NXP, however, the reflow process may cause an extra 0.5% drift at the room temperature.
- 7. This specification applies to any time the FLL reference source or reference divider is changed, trim value changed, or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- 8. Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f<sub>Bus</sub>. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V<sub>DD</sub> and V<sub>SS</sub> and variation in crystal oscillator frequency increase the C<sub>Jitter</sub> percentage for a given interval.

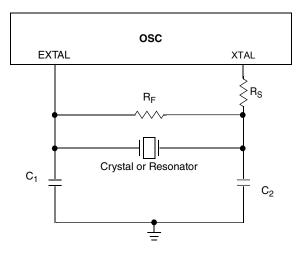


Figure 15. Typical crystal or resonator circuit

## 6.3 NVM specifications

This section provides details about program/erase times and program/erase endurance for the flash and EEPROM memories.

Table 13. Flash and EEPROM characteristics

С	Characteristic	Symbol	Min <sup>1</sup>	Typical <sup>2</sup>	Max <sup>3</sup>	Unit <sup>4</sup>
D	Supply voltage for program/erase –40 °C to 105 °C	V <sub>prog/erase</sub>	2.7	_	5.5	V

Table 13. Flash and EEPROM characteristics (continued)

С	Characteristic	Symbol	Min <sup>1</sup>	Typical <sup>2</sup>	Max <sup>3</sup>	Unit <sup>4</sup>
D	Supply voltage for read operation	V <sub>Read</sub>	2.7	_	5.5	V
D	NVM Bus frequency	f <sub>NVMBUS</sub>	1	_	25	MHz
D	NVM Operating frequency	f <sub>NVMOP</sub>	0.8	1	1.05	MHz
D	Erase Verify All Blocks	t <sub>VFYALL</sub>	_	_	17338	t <sub>cyc</sub>
D	Erase Verify Flash Block	t <sub>RD1BLK</sub>	_	_	16913	t <sub>cyc</sub>
D	Erase Verify EEPROM Block	t <sub>RD1BLK</sub>	_	_	810	t <sub>cyc</sub>
D	Erase Verify Flash Section	t <sub>RD1SEC</sub>	_	_	484	t <sub>cyc</sub>
D	Erase Verify EEPROM Section	t <sub>DRD1SEC</sub>	_	_	555	t <sub>cyc</sub>
D	Read Once	t <sub>RDONCE</sub>	_	_	450	t <sub>cyc</sub>
D	Program Flash (2 word)	t <sub>PGM2</sub>	0.12	0.12	0.29	ms
D	Program Flash (4 word)	t <sub>PGM4</sub>	0.20	0.21	0.46	ms
D	Program Once	t <sub>PGMONCE</sub>	0.20	0.21	0.21	ms
D	Program EEPROM (1 Byte)	t <sub>DPGM1</sub>	0.10	0.10	0.27	ms
D	Program EEPROM (2 Byte)	t <sub>DPGM2</sub>	0.17	0.18	0.43	ms
D	Program EEPROM (3 Byte)	t <sub>DPGM3</sub>	0.25	0.26	0.60	ms
D	Program EEPROM (4 Byte)	t <sub>DPGM4</sub>	0.32	0.33	0.77	ms
D	Erase All Blocks	t <sub>ERSALL</sub>	96.01	100.78	101.49	ms
D	Erase Flash Block	t <sub>ERSBLK</sub>	95.98	100.75	101.44	ms
D	Erase Flash Sector	t <sub>ERSPG</sub>	19.10	20.05	20.08	ms
D	Erase EEPROM Sector	t <sub>DERSPG</sub>	4.81	5.05	20.57	ms
D	Unsecure Flash	t <sub>UNSECU</sub>	96.01	100.78	101.48	ms
D	Verify Backdoor Access Key	t <sub>VFYKEY</sub>	_	_	464	t <sub>cyc</sub>
D	Set User Margin Level	t <sub>MLOADU</sub>	_	_	407	t <sub>cyc</sub>
С	FLASH Program/erase endurance $T_L$ to $T_H$ = -40 °C to 105 °C	n <sub>FLPE</sub>	10 k	100 k	_	Cycles
С	EEPROM Program/erase endurance TL to TH = -40 °C to 105 °C	n <sub>FLPE</sub>	50 k	500 k	_	Cycles
С	Data retention at an average junction temperature of T <sub>Javg</sub> = 85°C after up to 10,000 program/erase cycles	t <sub>D_ret</sub>	15	100	_	years

<sup>1.</sup> Minimum times are based on maximum  $f_{\mbox{\scriptsize NVMOP}}$  and maximum  $f_{\mbox{\scriptsize NVMBUS}}$ 

Program and erase operations do not require any special power sources other than the normal  $V_{DD}$  supply. For more detailed information about program/erase operations, see the Flash Memory Module section in the reference manual.

<sup>2.</sup> Typical times are based on typical f<sub>NVMOP</sub> and maximum f<sub>NVMBUS</sub>

<sup>3.</sup> Maximum times are based on typical  $f_{NVMOP}$  and typical  $f_{NVMBUS}$  plus aging

<sup>4.</sup>  $t_{cyc} = 1 / f_{NVMBUS}$ 

# 6.4 Analog

## 6.4.1 ADC characteristics

Table 14. 5 V 12-bit ADC operating conditions

Characteri stic	Conditions	Symbol	Min	Typ <sup>1</sup>	Max	Unit	Comment
Reference	• Low	V <sub>REFL</sub>	V <sub>SSA</sub>	_	$V_{SSA}$	V	_
potential	• High	V <sub>REFH</sub>	$V_{DDA}$	_	$V_{DDA}$		
Supply	Absolute	V <sub>DDA</sub>	2.7	_	5.5	V	_
voltage	Delta to V <sub>DD</sub> (V <sub>DD</sub> -V <sub>DDA</sub> )	$\Delta V_{DDA}$	-100	0	+100	mV	_
Ground voltage	Delta to V <sub>SS</sub> (V <sub>SS</sub> -V <sub>SSA</sub> )	ΔV <sub>SSA</sub>	-100	0	+100	mV	_
Input voltage		V <sub>ADIN</sub>	$V_{REFL}$	_	V <sub>REFH</sub>	V	_
Input capacitance		C <sub>ADIN</sub>	_	4.5	5.5	pF	_
Input resistance		R <sub>ADIN</sub>	_	3	5	kΩ	_
Analog source	12-bit mode • f <sub>ADCK</sub> > 4 MHz	R <sub>AS</sub>	_	_	2	kΩ	External to MCU
resistance	• f <sub>ADCK</sub> < 4 MHz		_	_	5		
	10-bit mode • f <sub>ADCK</sub> > 4 MHz		_	_	5		
	• f <sub>ADCK</sub> < 4 MHz		_	_	10		
	8-bit mode		_	_	10		
	(all valid f <sub>ADCK</sub> )						
ADC	High speed (ADLPC=0)	f <sub>ADCK</sub>	0.4	_	8.0	MHz	_
conversion clock frequency	Low power (ADLPC=1)		0.4	_	4.0		

<sup>1.</sup> Typical values assume  $V_{DDA} = 5.0 \text{ V}$ , Temp = 25°C,  $f_{ADCK} = 1.0 \text{ MHz}$  unless otherwise stated. Typical values are for reference only and are not tested in production.

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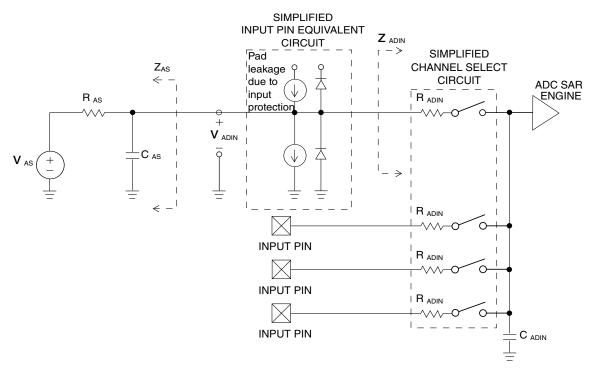


Figure 16. ADC input impedance equivalency diagram

Table 15. 12-bit ADC characteristics ( $V_{REFH} = V_{DDA}$ ,  $V_{REFL} = V_{SSA}$ )

Characteristic	Conditions	С	Symbol	Min	Typ <sup>1</sup>	Max	Unit
Supply current		T	I <sub>DDA</sub>	_	133	_	μΑ
ADLPC = 1							
ADLSMP = 1							
ADCO = 1							
Supply current		Т	I <sub>DDA</sub>	_	218	_	μΑ
ADLPC = 1							
ADLSMP = 0							
ADCO = 1							
Supply current		Т	I <sub>DDA</sub>	_	327	_	μΑ
ADLPC = 0							
ADLSMP = 1							
ADCO = 1							
Supply current		Т	I <sub>DDA</sub>	_	582	990	μΑ
ADLPC = 0							
ADLSMP = 0							
ADCO = 1							
Supply current	Stop, reset, module off	Т	I <sub>DDA</sub>	_	0.011	1	μΑ
ADC asynchronous clock source	High speed (ADLPC = 0)	Р	f <sub>ADACK</sub>	2	3.3	5	MHz

Table 15. 12-bit ADC characteristics ( $V_{REFH} = V_{DDA}$ ,  $V_{REFL} = V_{SSA}$ ) (continued)

Characteristic	Conditions	С	Symbol	Min	Typ <sup>1</sup>	Max	Unit
	Low power (ADLPC = 1)			1.25	2	3.3	
Conversion time (including sample	Short sample (ADLSMP = 0)	Т	t <sub>ADC</sub>	_	20	_	ADCK cycles
time)	Long sample (ADLSMP = 1)			_	40	_	
Sample time	Short sample (ADLSMP = 0)	Т	t <sub>ADS</sub>	_	3.5	_	ADCK cycles
	Long sample (ADLSMP = 1)			_	23.5	_	
Total unadjusted Error <sup>2</sup>	12-bit mode <sup>3</sup>	Т	E <sub>TUE</sub>	_	±3.6	_	LSB <sup>4</sup>
	10-bit mode	Р		_	±1.5	±2.0	
	8-bit mode	Т		_	±0.7	±1.0	
Differential Non- Liniarity	12-bit mode	Т	DNL	_	±1.0	_	LSB <sup>4</sup>
	10-bit mode <sup>5</sup>	Р		_	±0.25	±0.5	
	8-bit mode <sup>5</sup>	Т		_	±0.15	±0.25	
Integral Non-Linearity	12-bit mode <sup>3</sup>	Т	INL	_	±1.0	_	LSB <sup>4</sup>
	10-bit mode	Т		_	±0.3	±0.5	
	8-bit mode	Т		_	±0.15	±0.25	
Zero-scale error <sup>6</sup>	12-bit mode	С	E <sub>zs</sub>	_	±2.0	_	LSB <sup>4</sup>
	10-bit mode	Р		_	±0.25	±1.0	
	8-bit mode	Т		_	±0.65	±1.0	
Full-scale error <sup>7</sup>	12-bit mode	Т	E <sub>FS</sub>	_	±2.5	_	LSB <sup>4</sup>
	10-bit mode	Т		_	±0.5	±1.0	
	8-bit mode	Т		_	±0.5	±1.0	
Quantization error	≤12 bit modes	D	EQ	_	_	±0.5	LSB <sup>4</sup>
Input leakage error <sup>8</sup>	all modes	D	E <sub>IL</sub>		I <sub>In</sub> * R <sub>AS</sub>		mV
Temp sensor slope	-40 °C–25 °C	D	m	_	3.266	_	mV/°C
	25 °C–125 °C			_	3.638	_	
Temp sensor voltage	25 °C	D	V <sub>TEMP25</sub>	_	1.396	_	V

<sup>1.</sup> Typical values assume  $V_{DDA} = 5.0 \text{ V}$ , Temp = 25 °C,  $f_{ADCK} = 1.0 \text{ MHz}$  unless otherwise stated. Typical values are for reference only and are not tested in production.

<sup>2.</sup> Includes quantization

<sup>3.</sup> This parameter is valid for the temperature range of 25  $^{\circ}\text{C}$  to 50  $^{\circ}\text{C}.$ 

<sup>4.</sup>  $1 LSB = (V_{REFH} - V_{REFL})/2^N$ 

<sup>5.</sup> Monotonicity and no-missing-codes guaranteed in 10-bit and 8-bit modes

<sup>6.</sup>  $V_{ADIN} = V_{SSA}$ 

<sup>7.</sup>  $V_{ADIN} = V_{DDA}$ 

<sup>8.</sup> I<sub>In</sub> = leakage current (refer to DC characteristics)

#### 6.4.2 Analog comparator (ACMP) electricals

Table 16. Comparator electrical specifications

С	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	$V_{DDA}$	2.7	_	5.5	V
Т	Supply current (Operation mode)	I <sub>DDA</sub>	_	10	20	μΑ
D	Analog input voltage	V <sub>AIN</sub>	V <sub>SS</sub> - 0.3	_	$V_{DDA}$	V
Р	Analog input offset voltage	V <sub>AIO</sub>	_	_	40	mV
С	Analog comparator hysteresis (HYST=0)	$V_{H}$	_	15	20	mV
С	Analog comparator hysteresis (HYST=1)	$V_{H}$	_	20	30	mV
Т	Supply current (Off mode)	I <sub>DDAOFF</sub>	_	60	_	nA
С	Propagation Delay	t <sub>D</sub>	_	0.4	1	μs

## 6.5 Communication interfaces

## 6.5.1 SPI switching specifications

The serial peripheral interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's reference manual for information about the modified transfer formats used for communicating with slower peripheral devices. All timing is shown with respect to 20%  $V_{DD}$  and 80%  $V_{DD}$ , unless noted, and 25 pF load on all SPI pins. All timing assumes high-drive strength is enabled for SPI output pins.

Table 17. SPI master mode timing

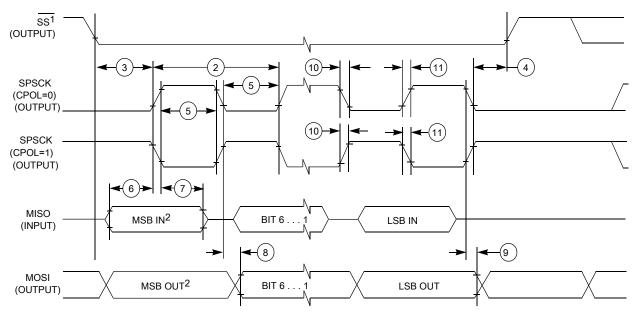
Nu m.	Symbol	Description	Min.	Max.	Unit	Comment
1	f <sub>op</sub>	Frequency of operation	f <sub>Bus</sub> /2048	f <sub>Bus</sub> /2	Hz	f <sub>Bus</sub> is the bus clock
2	t <sub>SPSCK</sub>	SPSCK period	2 x t <sub>Bus</sub>	2048 x t <sub>Bus</sub>	ns	$t_{Bus} = 1/f_{Bus}$
3	t <sub>Lead</sub>	Enable lead time	1/2	_	t <sub>SPSCK</sub>	_
4	t <sub>Lag</sub>	Enable lag time	1/2	_	t <sub>SPSCK</sub>	_
5	t <sub>WSPSCK</sub>	Clock (SPSCK) high or low time	t <sub>Bus</sub> – 30	1024 x t <sub>Bus</sub>	ns	_
6	t <sub>SU</sub>	Data setup time (inputs)	8	_	ns	_
7	t <sub>HI</sub>	Data hold time (inputs)	8	_	ns	_
8	t <sub>v</sub>	Data valid (after SPSCK edge)	_	25	ns	_
9	t <sub>HO</sub>	Data hold time (outputs)	20	_	ns	_
10	t <sub>RI</sub>	Rise time input	_	t <sub>Bus</sub> – 25	ns	_

Table continues on the next page...

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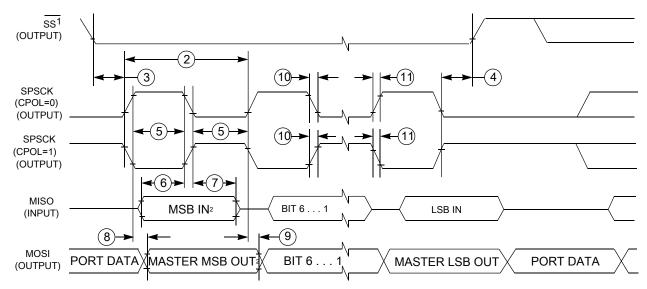
Table 17. SPI master mode timing (continued)

Nu m.	Symbol	Description	Min.	Max.	Unit	Comment
	t <sub>FI</sub>	Fall time input				
11	t <sub>RO</sub>	Rise time output	_	25	ns	_
	t <sub>FO</sub>	Fall time output				



- 1. If configured as an output.
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 17. SPI master mode timing (CPHA=0)



- 1.If configured as output
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 18. SPI master mode timing (CPHA=1)

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Table 18. SPI slave mode timing

Nu m.	Symbol	Description	Min.	Max.	Unit	Comment
1	f <sub>op</sub>	Frequency of operation	0	f <sub>Bus</sub> /4	Hz	f <sub>Bus</sub> is the bus clock as defined in Control timing.
2	t <sub>SPSCK</sub>	SPSCK period	4 x t <sub>Bus</sub>	_	ns	$t_{Bus} = 1/f_{Bus}$
3	t <sub>Lead</sub>	Enable lead time	1	_	t <sub>Bus</sub>	_
4	t <sub>Lag</sub>	Enable lag time	1	_	t <sub>Bus</sub>	_
5	twspsck	Clock (SPSCK) high or low time	t <sub>Bus</sub> - 30	_	ns	_
6	t <sub>SU</sub>	Data setup time (inputs)	15	_	ns	_
7	t <sub>HI</sub>	Data hold time (inputs)	25	_	ns	_
8	t <sub>a</sub>	Slave access time	_	t <sub>Bus</sub>	ns	Time to data active from high-impedance state
9	t <sub>dis</sub>	Slave MISO disable time	_	t <sub>Bus</sub>	ns	Hold time to high- impedance state
10	t <sub>v</sub>	Data valid (after SPSCK edge)	_	25	ns	_
11	t <sub>HO</sub>	Data hold time (outputs)	0	_	ns	_
12	t <sub>RI</sub>	Rise time input	_	t <sub>Bus</sub> - 25	ns	_
	t <sub>FI</sub>	Fall time input				
13	t <sub>RO</sub>	Rise time output	_	25	ns	_
	t <sub>FO</sub>	Fall time output				

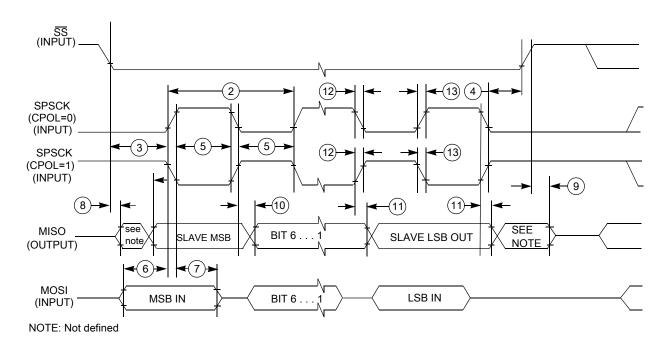


Figure 19. SPI slave mode timing (CPHA = 0)

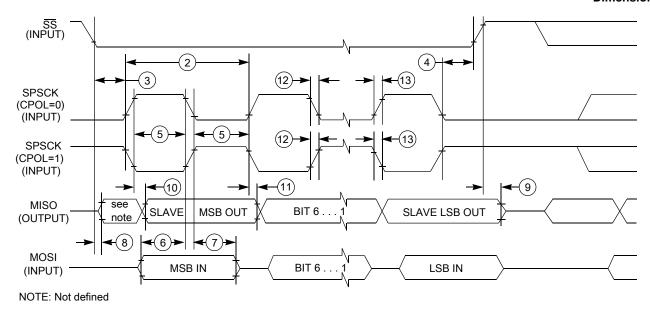


Figure 20. SPI slave mode timing (CPHA=1)

#### 7 Dimensions

# 7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to **nxp.com** and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
32-pin LQFP	98ASH70029A
32-pin QFN	98ASA00473D
44-pin LQFP	98ASS23225W
64-pin QFP	98ASB42844B
64-pin LQFP	98ASS23234W

#### 8 Pinout

# 8.1 Signal multiplexing and pin assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

Table 19. Pin availability by package pin-count

	Pin Number			Lowest	Priority <> H	ighest	
64-QFP/ LQFP	44-LQFP	32- LQFP/QFN	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
1	1	1	PTD1 <sup>1</sup>	KBI1_P1	FTM2_CH3	SPI1_MOSI	_
2	2	2	PTD0 <sup>1</sup>	KBI1_P0	FTM2_CH2	SPI1_SCK	_
3	_	_	PTH7	_	_	_	_
4	_	_	PTH6	_	_	_	_
5	3	_	PTE7	_	FTM2_CLK	_	FTM1_CH1
6	4	_	PTH2	_	BUSOUT	_	FTM1_CH0
7	5	3	_	_	_	_	VDD
8	6	4	_	_	_	VDDA	VREFH <sup>2</sup>
9	7	5	_	_	_	_	VREFL
10	8	6	_	_	_	VSSA	VSS <sup>3</sup>
11	9	7	PTB7	_	I2C0_SCL	_	EXTAL
12	10	8	PTB6	_	I2C0_SDA	_	XTAL
13	11	_	_	_	_	_	VSS
14	_	_	PTH1 <sup>1</sup>	_	FTM2_CH1	_	_
15	_	_	PTH0 <sup>1</sup>	_	FTM2_CH0	_	_
16	_	_	PTE6	_	_	_	_
17	_	_	PTE5	_	_	_	_
18	12	9	PTB5 <sup>1</sup>	FTM2_CH5	SPI0_PCS0	ACMP1_OUT	_
19	13	10	PTB4 <sup>1</sup>	FTM2_CH4	SPI0_MISO	NMI	ACMP1_IN2
20	14	11	PTC3	FTM2_CH3	_	_	ADC0_SE11
21	15	12	PTC2	FTM2_CH2	_	_	ADC0_SE10
22	16	_	PTD7	KBI1_P7	UART2_TX	_	_
23	17	_	PTD6	KBI1_P6	UART2_RX	_	_
24	18	_	PTD5	KBI1_P5	_	_	_
25	19	13	PTC1	_	FTM2_CH1	_	ADC0_SE9
26	20	14	PTC0	_	FTM2_CH0	_	ADC0_SE8
27	_	_	PTF7	_		_	ADC0_SE15

Table 19. Pin availability by package pin-count (continued)

Pin Number			Lowest Priority <> Highest				
64-QFP/ LQFP	44-LQFP	32- LQFP/QFN	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
28	_	_	PTF6	_	_	_	ADC0_SE14
29	_	_	PTF5	_	_	_	ADC0_SE13
30	_	_	PTF4	_	_	_	ADC0_SE12
31	21	15	PTB3	KBI0_P7	SPI0_MOSI	FTM0_CH1	ADC0_SE7
32	22	16	PTB2	KBI0_P6	SPI0_SCK	FTM0_CH0	ADC0_SE6
33	23	17	PTB1	KBI0_P5	UART0_TX	_	ADC0_SE5
34	24	18	PTB0	KBI0_P4	UART0_RX	_	ADC0_SE4
35	_	_	PTF3	_	_	_	_
36	_	_	PTF2	_	_	_	_
37	25	19	PTA7	_	FTM2_FLT2	ACMP1_IN1	ADC0_SE3
38	26	20	PTA6	_	FTM2_FLT1	ACMP1_IN0	ADC0_SE2
39	_	_	PTE4	_	_	_	_
40	27	_	_	_	_	_	VSS
41	28	_	_	_	_	_	VDD
42	_	_	PTF1	_	_	_	_
43	_	_	PTF0	_	_	_	_
44	29	_	PTD4	KBI1_P4	_	_	_
45	30	21	PTD3	KBI1_P3	SPI1_PCS0	_	_
46	31	22	PTD2	KBI1_P2	SPI1_MISO	_	_
47	32	23	PTA3 <sup>4</sup>	KBI0_P3	UART0_TX	I2C0_SCL	_
48	33	24	PTA2 <sup>4</sup>	KBI0_P2	UART0_RX	I2C0_SDA	_
49	34	25	PTA1	KBI0_P1	FTM0_CH1	ACMP0_IN1	ADC0_SE1
50	35	26	PTA0	KBI0_P0	FTM0_CH0	ACMP0_IN0	ADC0_SE0
51	36	27	PTC7	_	UART1_TX	_	_
52	37	28	PTC6	_	UART1_RX	_	_
53	_	_	PTE3	_	SPI0_PCS0	_	_
54	38	_	PTE2	_	SPI0_MISO	_	_
55	_	_	PTG3	_	_	_	_
56	_	_	PTG2	_	_	_	_
57	_	_	PTG1	_	_	_	_
58	_	_	PTG0	_	_	_	_
59	39	_	PTE1 <sup>1</sup>	_	SPI0_MOSI	_	_
60	40	_	PTE0 <sup>1</sup>	_	SPI0_SCK	FTM1_CLK	_
61	41	29	PTC5	_	FTM1_CH1	_	RTCO
62	42	30	PTC4	RTCO	FTM1_CH0	ACMP0_IN2	SWD_CLK
63	43	31	PTA5	IRQ	FTM0_CLK	_	RESET
64	44	32	PTA4	_	ACMP0_OUT	_	SWD_DIO

<sup>1.</sup> This is a high-current drive pin when operated as output.

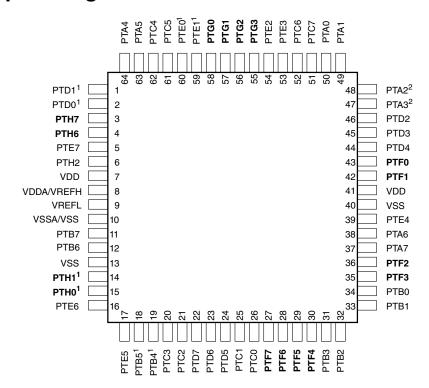
#### **Pinout**

- 2. VREFH and VDDA are internally connected.
- VSSA and VSS are internally connected.
- 4. This is a true open-drain pin when operated as output.

#### **Note**

When an alternative function is first enabled, it is possible to get a spurious edge to the module. User software must clear any associated flags before interrupts are enabled. Table 19 illustrates the priority if multiple modules are enabled. The highest priority module will have control over the pin. Selecting a higher priority pin function with a lower priority function already enabled can cause spurious edges to the lower priority module. Disable all modules that share a pin before enabling another module.

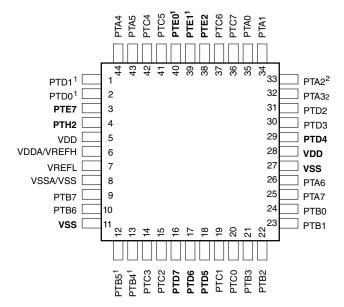
## 8.2 Device pin assignment



Pins in **bold** are not available on less pin-count packages.

- 1. High source/sink current pins
- 2. True open drain pins

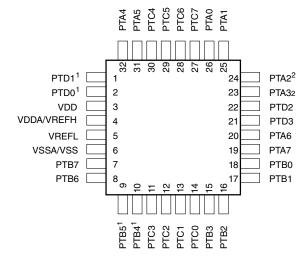
Figure 21. 64-pin QFP/LQFP packages



Pins in **bold** are not available on less pin-count packages.

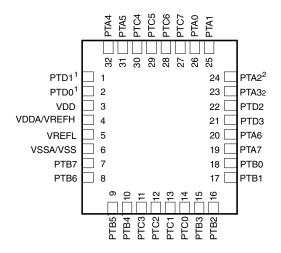
- 1. High source/sink current pins
- 2. True open drain pins

Figure 22. 44-pin LQFP package



- 1. High source/sink current pins
- 2. True open drain pins

Figure 23. 32-pin LQFP package



- 1. High source/sink current pins
- 2. True open drain pins

Figure 24. 32-pin QFN package

# 9 Revision history

The following table provides a revision history for this document.

Table 20. Revision history

Rev. No.	Date	Substantial Changes		
2	3/2014	Initial public release.		
3	10/2014	Added new package of 32-pin QFN information     Updated pin-out     Updated key features of UART, KBI and ADC in the front page     Added a note to the Max. in Supply current characteristics     Updated footnote f <sub>OSC</sub> = 10 MHz (crystal) in EMC radiated emissions operating behaviors     Added a new section of Thermal operating requirements     Updated NVM specifications     Added reference potential in ADC characteristics     Updated to "All timing assumes high-drive strength is enabled for SPI output pins." in SPI switching specifications		
4	07/2016	<ul> <li>Updated the Typical value of E<sub>TUE</sub> in 12-bit mode and added a note to the 12-bit mode of E<sub>TUE</sub> and INL in the ADC characteristics.</li> </ul>		
5	01/2019	<ul> <li>Added a footnote of "Max power suppply ramp rate is 500 V/ms." to         Operating voltage in the DC characteristics.</li> <li>Added a footnote to the Δf<sub>int_ft</sub> in the External oscillator (OSC) and         ICS characteristics</li> </ul>		
6	12/2019	<ul> <li>Updated the footnote to the Operating voltage in the DC characteristics.</li> </ul>		

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